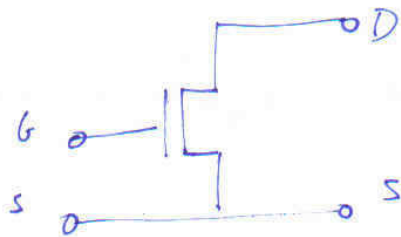
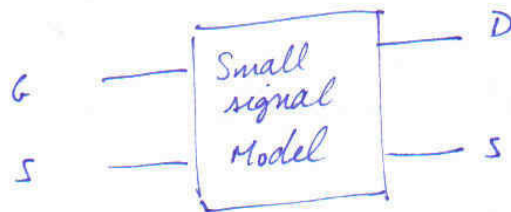


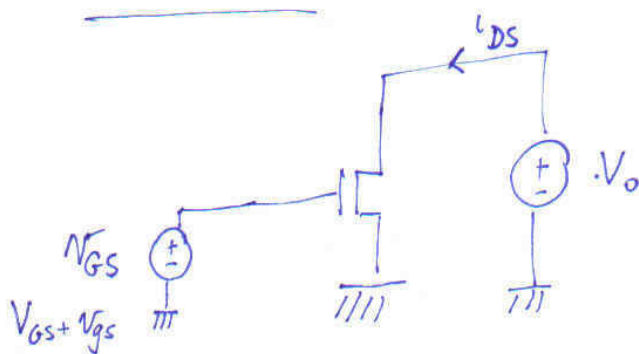
Model of Transistor: Lecture 13



\equiv



1st Setup:



$i_{DS} = \underbrace{I_{DS}}_{\text{bias point}} + \underbrace{i_{ds}}_{\text{desired signal: sine wave}}$

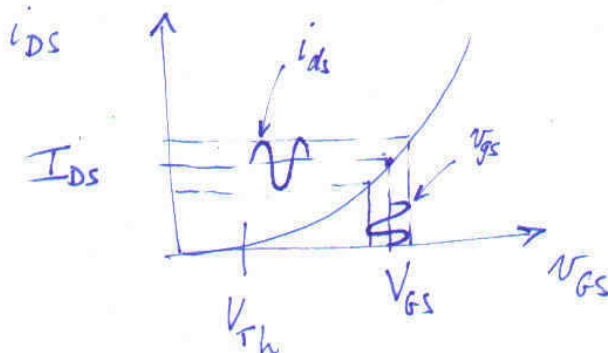
we know:

$$I_{DS} = \mu_n C_{ox} \frac{W}{2L} (V_{GS} - V_{Th})^2$$

(assuming $V_D > V_{GS} - V_{Th}$)

now how do we find i_{ds} ?

we know that i_{ds} is a function of V_{GS} :

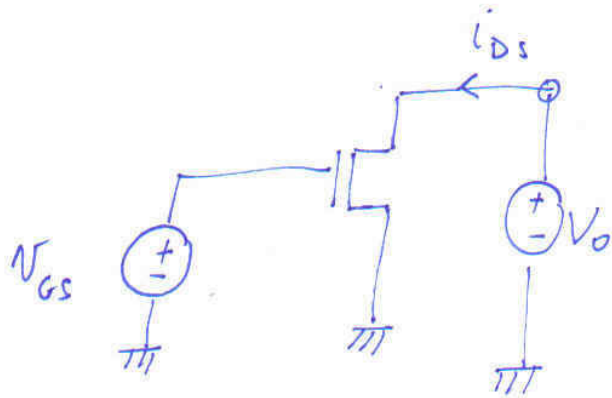


We can linearize the i_{DS} vs. V_{GS} curve around I_{DS}, V_{GS} and find the slope:

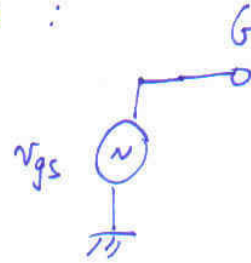
$$g_m = \frac{\partial i_{DS}}{\partial V_{GS}} \quad \text{for } V_{GS} \text{ small enough:}$$

$$i_{ds} \approx g_m \cdot v_{gs}$$

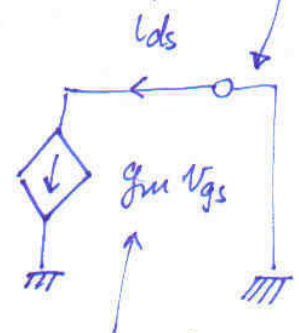
So we can therefore model :



as :



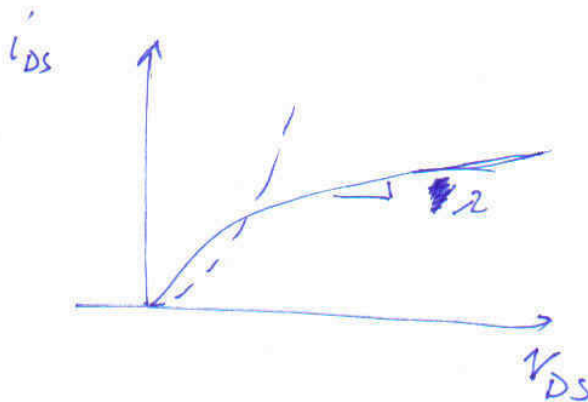
⚠ note : Small signal ground



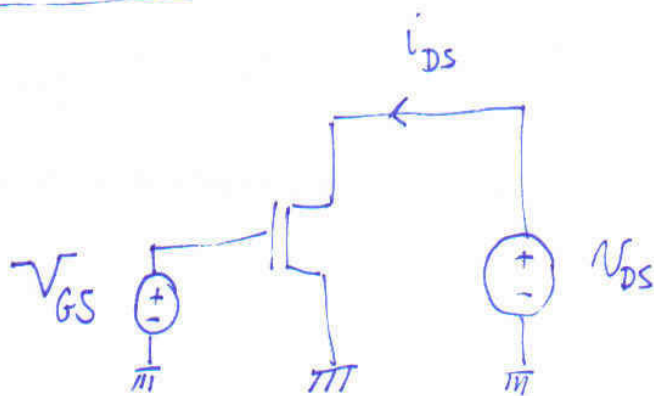
$$g_m = \frac{\partial i_{DS}}{\partial v_{GS}} \approx \frac{W}{L} \mu_n C_{ox} (V_{GS} - V_T)$$

the bias information is reflected in g_m .

2nd Setup : In the 1st experiment, we kept V_{DS} constant. We know that i_{DS} changes with V_{DS} as well :



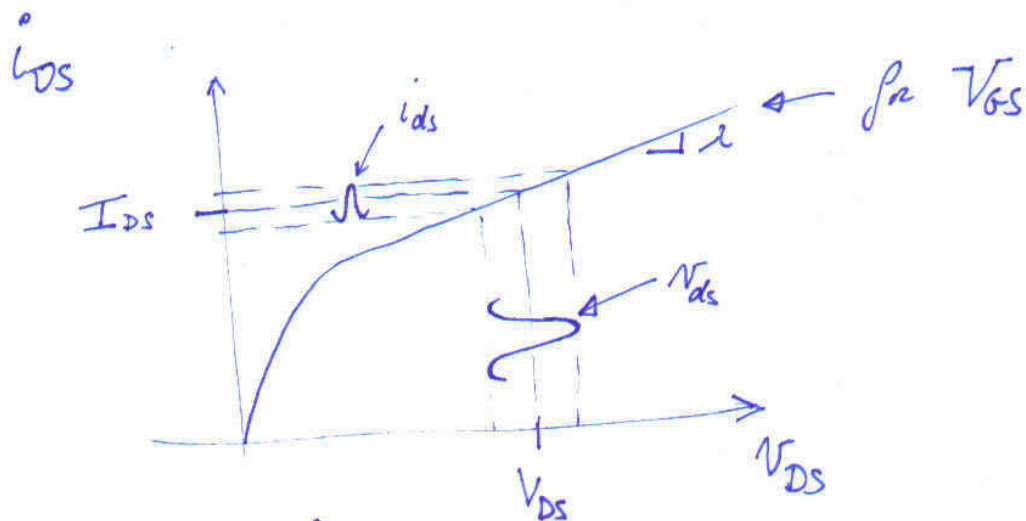
2nd Setup:



Assume V_{DS} is large enough to put transistor in saturation: $V_{DS} > V_{GS} - V_{TH}$

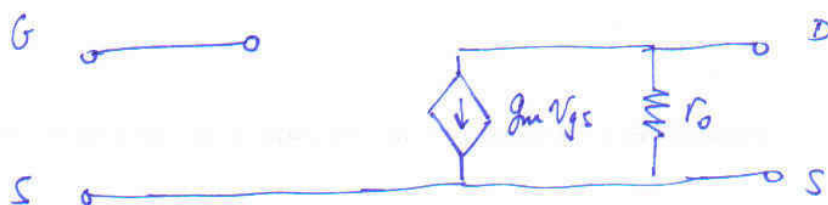
$$v_{DS} = V_{DS} + v_{ds}$$

$$i_{DS} = I_{DS} + i_{ds}$$



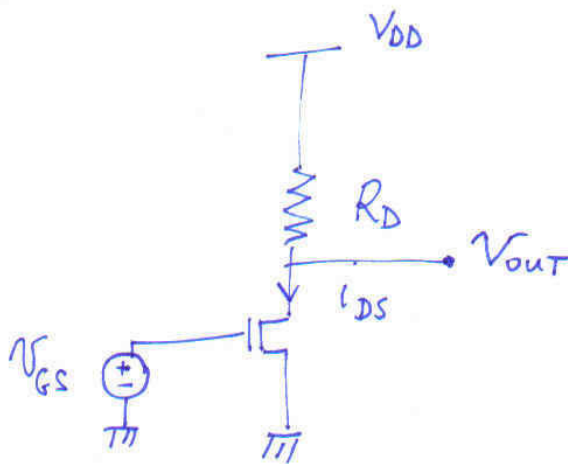
$$g_o = \frac{\partial i_{DS}}{\partial v_{DS}} \approx \lambda I_{DS}$$

$$\Rightarrow i_{ds} = g_o \cdot v_{ds} \quad \text{or} \quad r_o = \frac{1}{g_o} \quad \text{and we can write our complete model:}$$



only for small signals!

Application :



$$V_{OUT} = V_{DD} - R_D \cdot i_{DS}$$

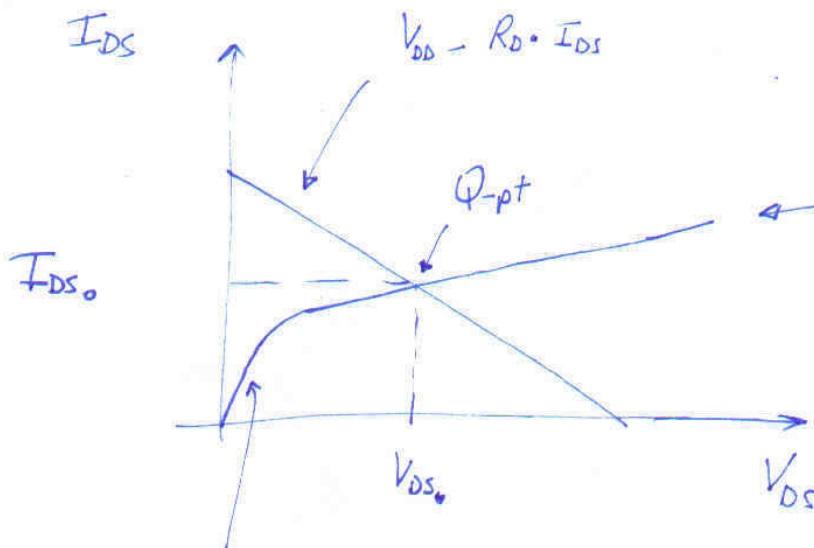
$$= \underbrace{V_{DD} - R_D \cdot I_{DS}}_{\text{DC Bias}} - \underbrace{R_D i_{ds}}_{\text{Small signal}}$$

$$V_{OUT} = V_{OUT} + v_{out}$$

$$\Rightarrow V_{OUT} = V_{DD} - R_D \cdot I_{DS}$$

how do we find the DC operating pt or Q-pt.?

→ load line: $V_{OUT} = V_{DS} = \underbrace{V_{DD} - R_D \cdot I_{DS}}_{\text{load line equation}}$



← for our V_{GS} .

⚠ note we are only looking @ DC values now. We will add the small signal by superposition

So now we have found our Q-pt.

next, we can find our small signal model:

$$g_m = \frac{\partial I_{DS}}{\partial V_{GS}} = \frac{W}{L} \mu_n C_{ox} (V_{GS} - V_{Th})$$

$$r_o = \left(\frac{\partial I_{DS}}{\partial V_{DS}} \right)^{-1} = \frac{1}{\lambda I_{DS}}$$

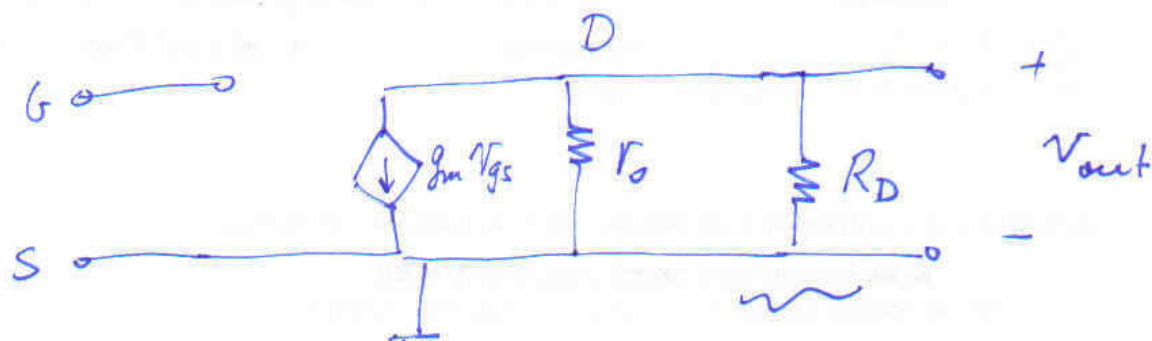
so now we have $V_{out} = -R_D \cdot i_{ds}$

$$= -R_D \cdot \left[g_m V_{gs} + \frac{V_{out}}{r_o} \right]$$

$$V_{out} \left[1 + \frac{R_D}{r_o} \right] = -R_D \cdot g_m V_{gs}$$

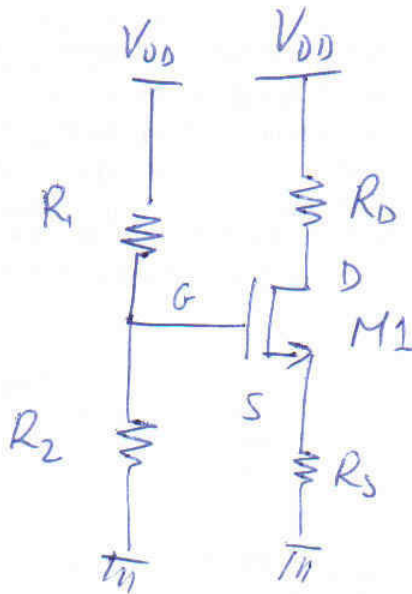
$$V_{out} = \underbrace{\frac{-r_o R_D}{r_o + R_D}}_{r_o \parallel R_D} \cdot g_m V_{gs}$$

more easily we could just have drawn



Lecture 14, slide 4:

1) DC Bias pt:

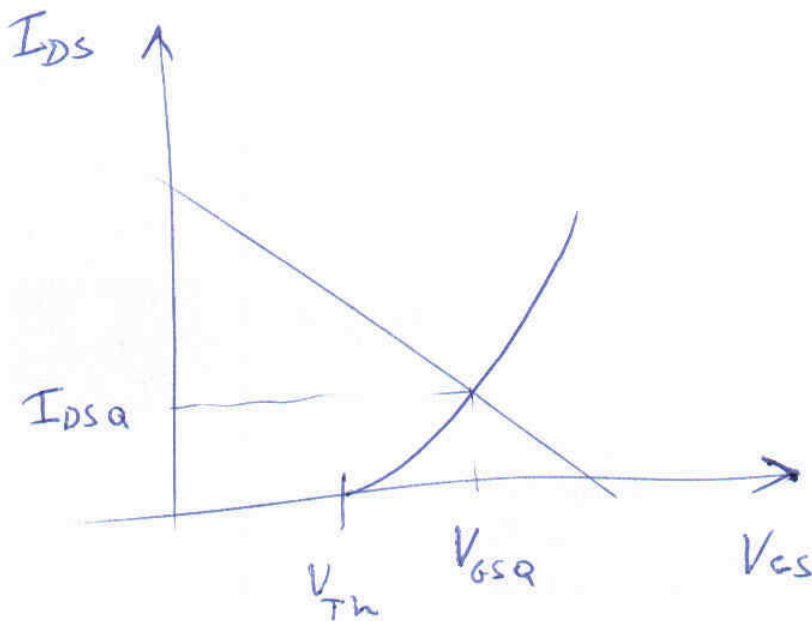


$$V_G = \frac{R_2}{R_1 + R_2} V_{DD}$$

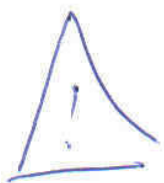
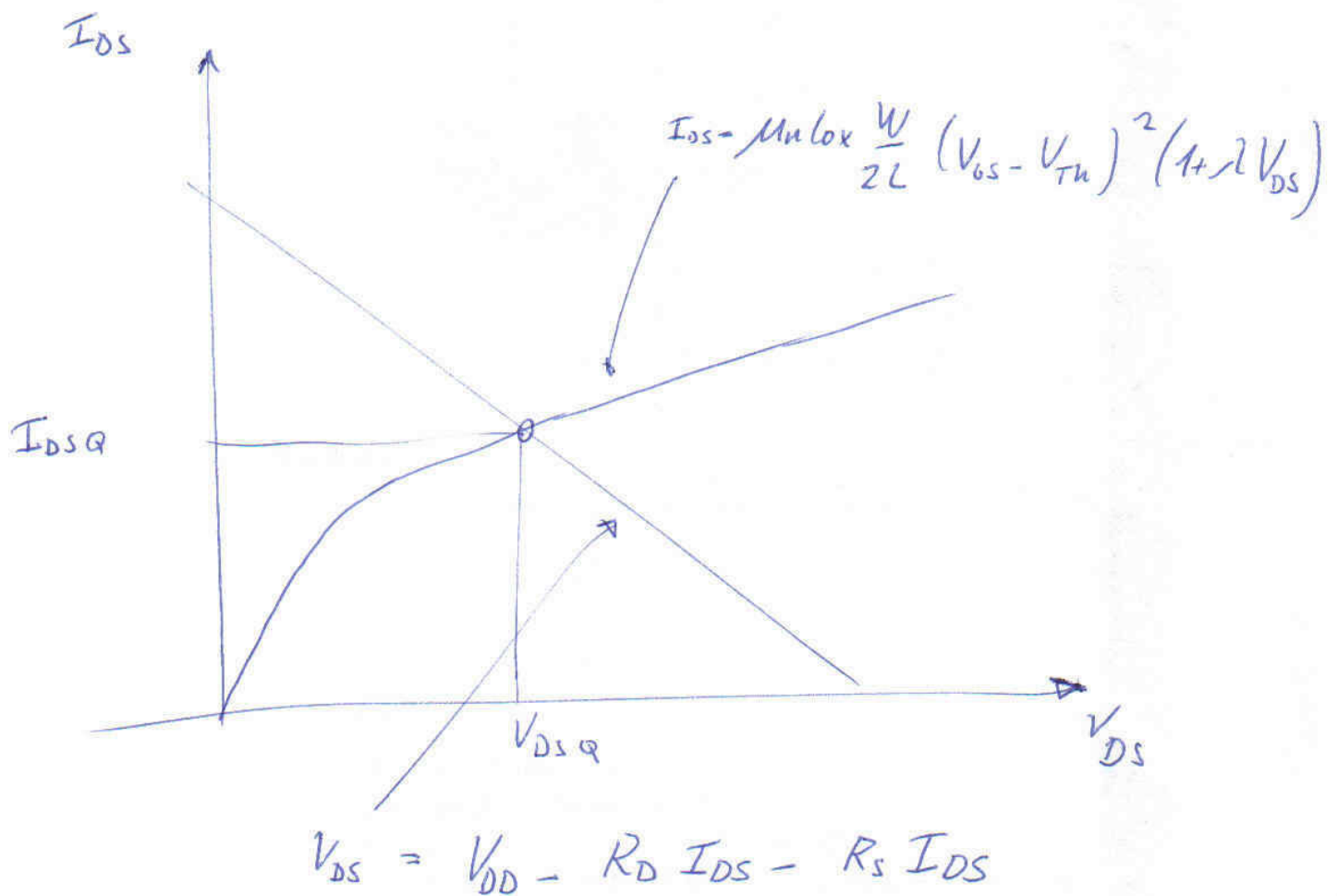
$$V_S = R_S \cdot I_{DS}$$

→ assume M1 is in saturation region

$$\Rightarrow I_{DS} = \mu_n C_{ox} \frac{W}{2L} (V_{GS} - V_{Th})^2$$



Find V_{DSQ} :



Note, this value of I_{DSQ} will be slightly different from the one found in the previous graph.

Do not worry about this small error since it won't affect the value of g_m greatly.

2) Double check $M1$ is in saturation: $V_{DSQ} > V_{GS} - V_{Th}$.

if $\lambda = 0$,

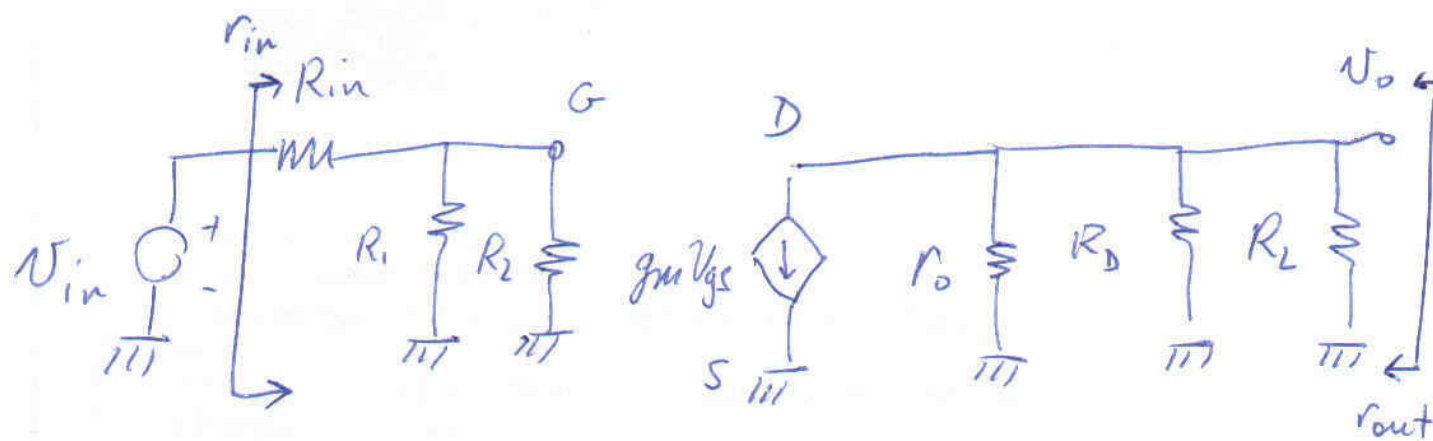
$$V_{DSQ} = V_{DD} - R_D \cdot I_{DSQ} - R_S \cdot I_{DSQ} > \underline{\underline{V_{GS} - V_{Th}}}$$

3) Find small signal parameters:

$$g_m = \mu_n C_{ox} \frac{W}{L} (V_{GSQ} - V_{Th}) \leftarrow \text{in saturation}$$

$$r_o = \frac{1}{\lambda I_{DSQ}}$$

1) Small signal model: Capacitors are short:



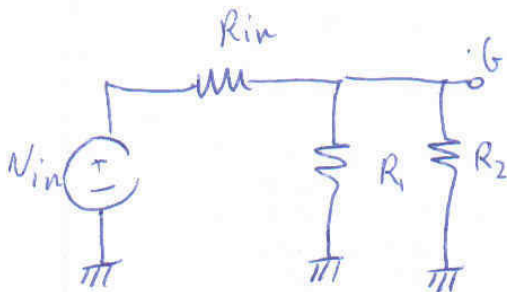
$$\frac{v_o}{v_{in}} = \frac{R_1 \parallel R_2}{R_{in} + (R_1 \parallel R_2)} \cdot (-g_m) \cdot (r_o \parallel R_D \parallel R_L)$$

$$r_{in} = R_{in} + (R_1 \parallel R_2)$$

$$r_{out} = r_o \parallel R_D \parallel R_L$$

Slide 9

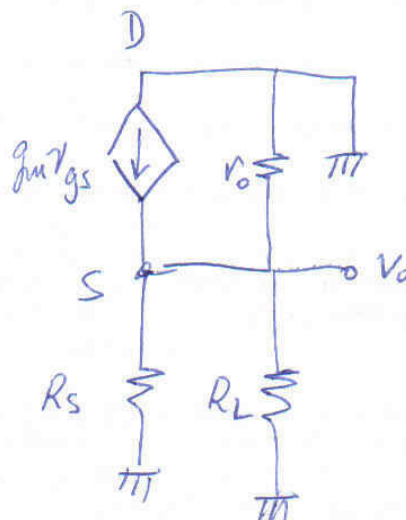
- 1) DC Bias pt: same as before
- 2) Double check region of operation of M1:
→ same as before
- 3) Small signal parameters: same as before
- 4) Small signal model:



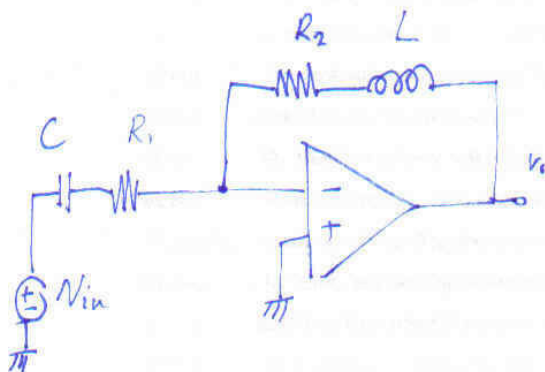
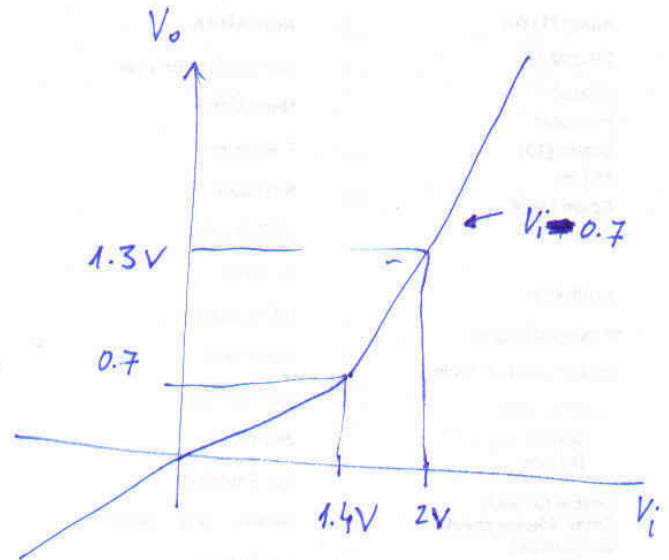
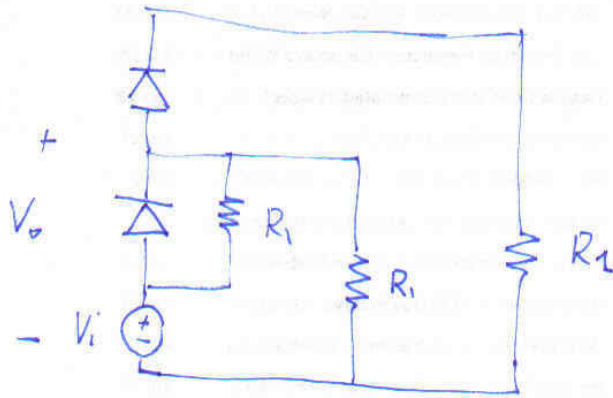
$$\frac{v_g}{v_{in}} = \frac{R_1 \parallel R_2}{(R_1 \parallel R_2) + R_{in}}$$

$$\begin{aligned} v_o &= g_m v_{gs} (r_o \parallel R_s \parallel R_L) \\ &= g_m v_g (r_o \parallel R_s \parallel R_L) - g_m v_o (R_L \parallel R_s \parallel r_o) \end{aligned}$$

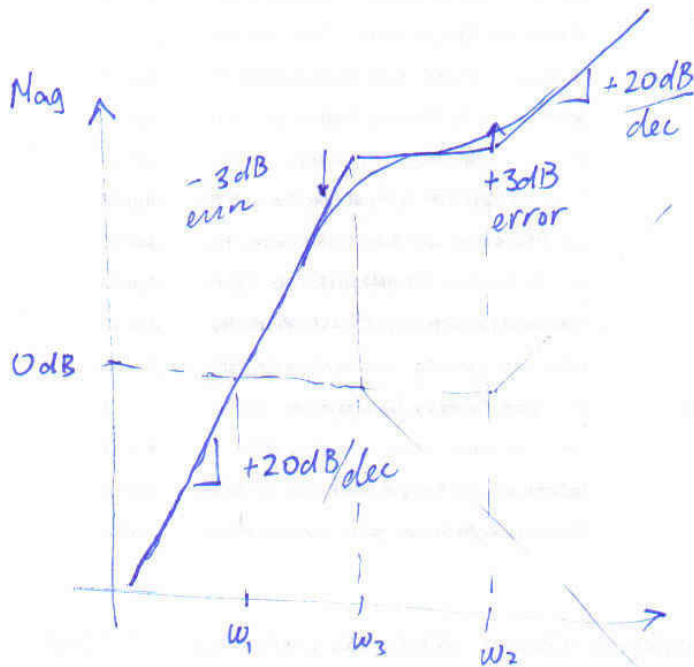
$$\frac{v_o}{v_g} = \frac{g_m (r_o \parallel R_s \parallel R_L)}{1 + g_m (r_o \parallel R_s \parallel R_L)} \approx 1 \quad \leftarrow \text{voltage buffer from } v_g \text{ to } v_o$$



Exam problems:



$$\begin{aligned} \frac{V_o}{V_{in}} &= \frac{-(R_2 + j\omega L)}{R_1 + \frac{1}{j\omega C}} \\ &= \frac{-j\omega C (R_2 + j\omega L)}{1 + j\omega R_1 C} \\ &= \frac{-j\omega R_2 C (1 + j\omega \frac{L}{R_2})}{1 + j\omega R_1 C} \\ &= \frac{-j\omega / \omega_1 (1 + j\omega / \omega_2)}{1 + j\omega / \omega_3} \end{aligned}$$

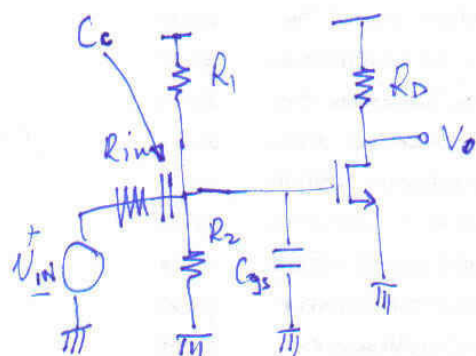
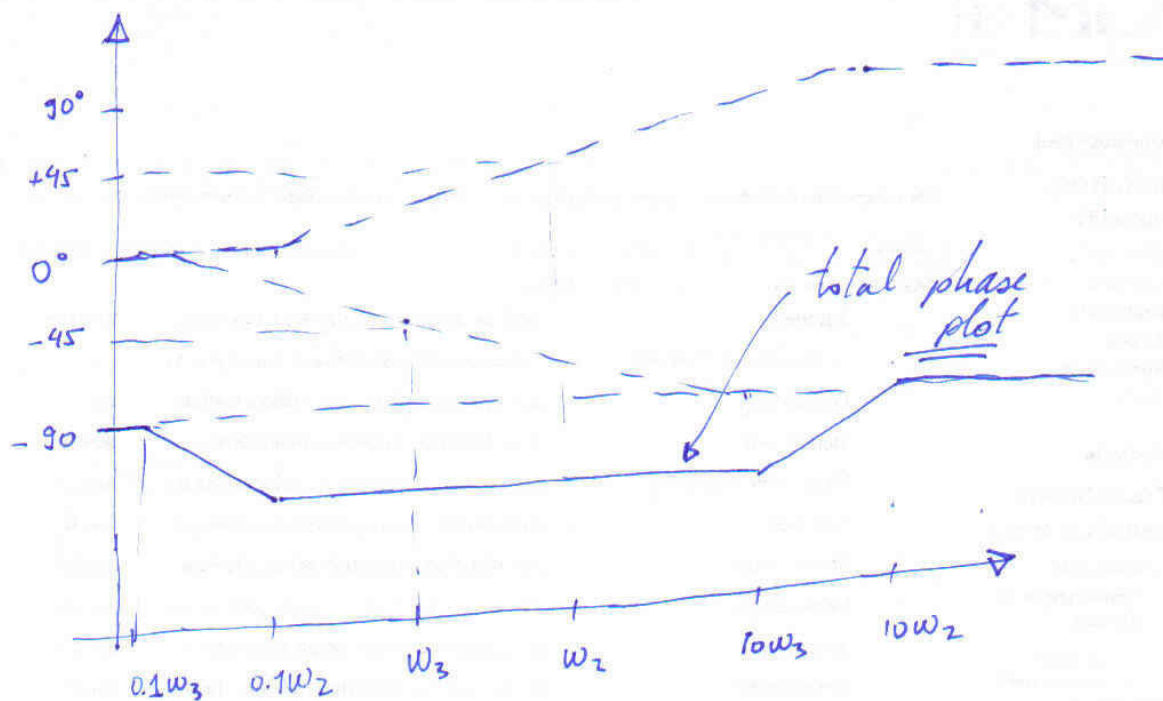


$$\omega_1 = \frac{1}{R_2 C}$$

$$\omega_2 = \frac{R_2}{L}$$

$$\omega_3 = \frac{1}{R_1 C}$$

$$L \frac{N_o}{N_{in}} (j\omega)$$



C_c is infinitely large,
 C_{gs} is not \Rightarrow include C_{gs} in SSM.

1.) Bias Pt: $V_{GSQ} = V_{DD} \cdot \frac{R_2}{R_1 + R_2}$

2) $g_m = \mu_n \text{ Cox } \frac{W}{L} (V_{GSQ} - V_{th})$

$r_o = \frac{1}{\lambda I_{DQ}}$ and $I_{DQ} = \mu_n \text{ Cox } \frac{W}{2L} (V_{GSQ} - V_{th})^2$

3) Small signal Model:

